



MMBT3906

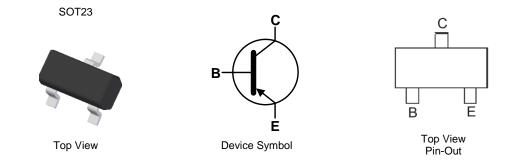
40V PNP SMALL SIGNAL TRANSISTOR IN SOT23

Features

- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Complementary NPN Type: MMBT3904
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)



Ordering Information (Notes 4 & 5)

Product	Status	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
MMBT3906-7-F	Active	AEC-Q101	K3N	7	8	3,000
MMBT3906Q-7-F	Active	Automotive	K3N	7	8	3,000
MMBT3906-13-F	Active	AEC-Q101	K3N	13	8	10,000

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

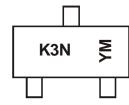
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.

5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



K3N = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: D = 2016) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

Year	2015	20	016	2017	2	018	2019	:	2020	2021		2022
Code	С		D	E		F	G		Н	I		J
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code								•	•	<u> </u>		



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-6.0	V
Collector Current	Ic	-200	mA
Peak Collector Current	I _{CM}	-200	mA
Peak Base Current	I _{BM}	-100	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 6)	Р	310	mW
	(Note 7)	PD	350	TTIVV
Thermal Desistance, Junction to Ambient	(Note 6)	P	403	°C/W
Thermal Resistance, Junction to Ambient	(Note 7)	R _{θJA}	357	°C/w
Thermal Resistance, Junction to Leads	(Note 8)	R _{θJL}	350	°C/W
Operating and Storage Temperature Range		T _J ,T _{STG}	-55 to +150	°C

ESD Ratings (Note 9)

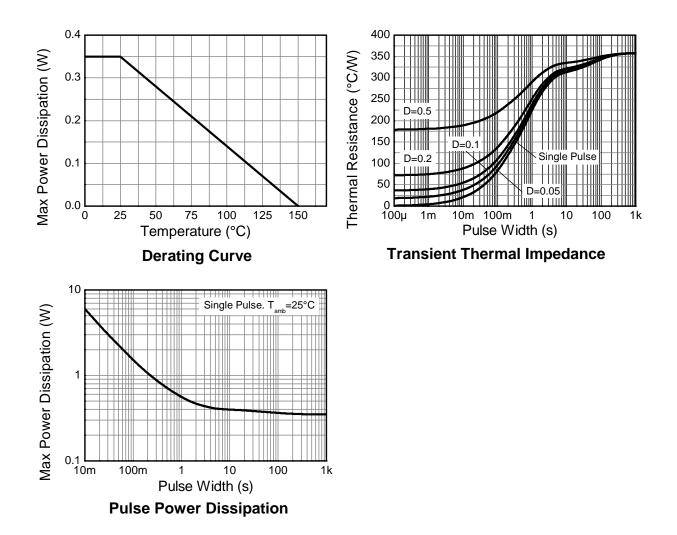
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

6. For a device mounted on minimum recommended pad layout 1oz copper that is on a single-sided FR4 PCB; device is measured under still air conditions whilst operating in a steady-state. Notes:

Same as note (6), except the device is mounted on 15 mm x 15mm 1oz copper.
 Thermal resistance from junction to solder-point (at the end of the leads).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





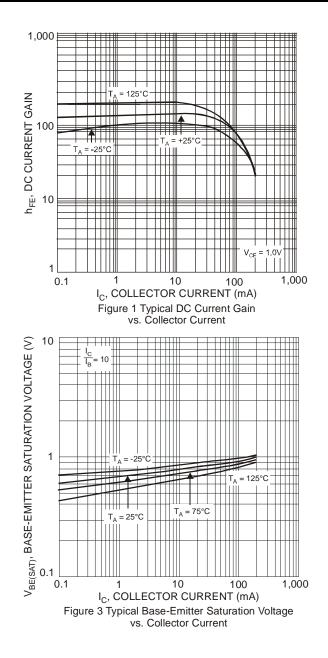
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

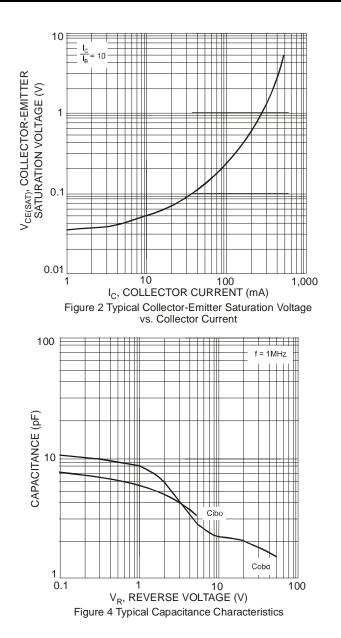
Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS			1	1	
Collector-Base Breakdown Voltage	BV _{CBO}	-40		V	$I_{\rm C} = -100 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-40	_	V	$I_{\rm C} = -10 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	BV _{EBO}	-6.0	_	V	$I_{\rm E} = -100 \mu A, I_{\rm C} = 0$
Collector Cutoff Current		_	-50	nA	$V_{CE} = -30V, V_{BE} = 3.0V$
	ICEV	_	-50	nA	$V_{CE} = -30V, V_{BE} = -0.25V$
Emitter-Base Cutoff Current	I _{EBO}	—	-50	nA	$V_{EB} = -5V$
ON CHARACTERISTICS (Note 10)					
DC Current Gain	h _{FE}	60 80 100 60 30	 300 	_	$\begin{split} I_{C} &= -100 \mu A, \ V_{CE} &= -1.0V \\ I_{C} &= -1.0mA, \ V_{CE} &= -1.0V \\ I_{C} &= -10mA, \ V_{CE} &= -1.0V \\ I_{C} &= -50mA, \ V_{CE} &= -1.0V \\ I_{C} &= -100mA, \ V_{CE} &= -1.0V \end{split}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}		-0.25 -0.40	V	$I_{C} = -10mA$, $I_{B} = -1.0mA$ $I_{C} = -50mA$, $I_{B} = -5.0mA$
Base-Emitter Saturation Voltage	V _{BE(sat)}	-0.65	-0.85 -0.95	V	$I_{C} = -10mA$, $I_{B} = -1.0mA$ $I_{C} = -50mA$, $I_{B} = -5.0mA$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	Cobo	_	4.5	pF	$V_{CB} = -5.0V, f = 1.0MHz, I_E = 0$
Input Capacitance	Cibo		10	pF	$V_{EB} = -0.5V$, f = 1.0MHz, I _C = 0
Input Impedance	h _{ie}	2.0	12	kΩ	
Voltage Feedback Ratio	h _{re}	0.1	10	x 10 ⁻⁴	$V_{CE} = 10V, I_C = 1.0mA,$
Small Signal Current Gain	h _{fe}	100	400	—	f = 1.0kHz
Output Admittance	h _{oe}	3.0	60	μS	
Current Gain-Bandwidth Product	fT	250		MHz	$V_{CE} = -20V, I_C = -10mA,$ f = 100MHz
Noise Figure	NF	_	4.0	dB	$V_{CE} = -5.0V, I_C = -100\mu A,$ $R_S = 1.0k\Omega, f = 1.0kHz$
SWITCHING CHARACTERISTICS					· · · ·
Delay Time	t _d		35	ns	$V_{CC} = -3.0V, I_{C} = -10mA,$
Rise Time	tr	—	35	ns	$V_{BE(off)} = 0.5V, I_{B1} = -1.0mA$
Storage Time	ts	_	225	ns	$V_{CC} = -3.0V, I_{C} = -10mA,$
Fall Time	t _f	_	75	ns	$I_{B1} = I_{B2} = -1.0 \text{mA}$

Note: 10. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.



Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

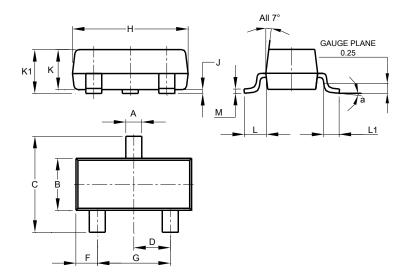






Package Outline Dimensions

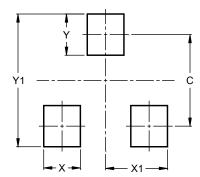
Please see http://www.diodes.com/package-outlines.html for the latest version.



	SOT23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
Μ	0.085	0.150	0.110				
а	0°	8°					
All	Dimens	ions in	mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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